

Erratum to: Enhancement of device performance by using quaternary capping over ternary capping in strain-coupled InAs/GaAs quantum dot infrared photodetectors

B. Tongbram¹ · S. Shetty¹ · H. Ghadi¹ · S. Adhikary¹ · S. Chakrabarti¹

Published online: 20 April 2017
© Springer-Verlag Berlin Heidelberg 2017

Erratum to: Appl. Phys. A (2015) 118:511–517
DOI [10.1007/s00339-014-8854-9](https://doi.org/10.1007/s00339-014-8854-9)

The original version of this article unfortunately contained a mistake. The captions to Figs. 3 and 4 were interchanged. The correct versions are given below.

The online version of the original article can be found under
doi:[10.1007/s00339-014-8854-9](https://doi.org/10.1007/s00339-014-8854-9).

✉ S. Chakrabarti
subho@ee.iitb.ac.in; subhanandachakrabarti@gmail.com

¹ Department of Electrical Engineering, Indian
Institute of Technology Bombay, Powai, Mumbai,
Maharashtra 400076, India

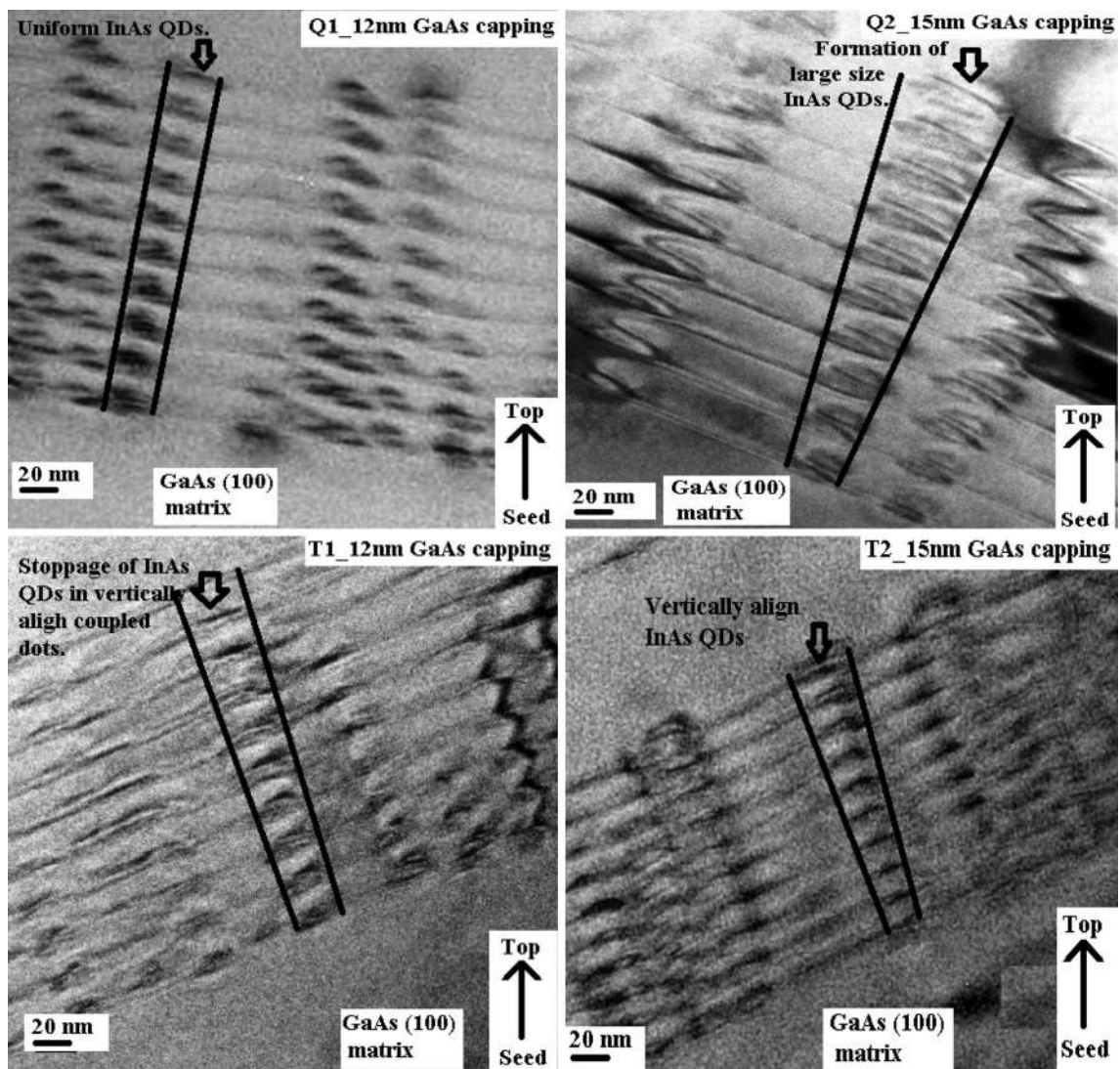


Fig. 3 Cross-sectional TEM images of all coupled samples. The average QD heights were 9, 11, 4, and 5 nm for samples Q1, Q2, T1, and T2, respectively

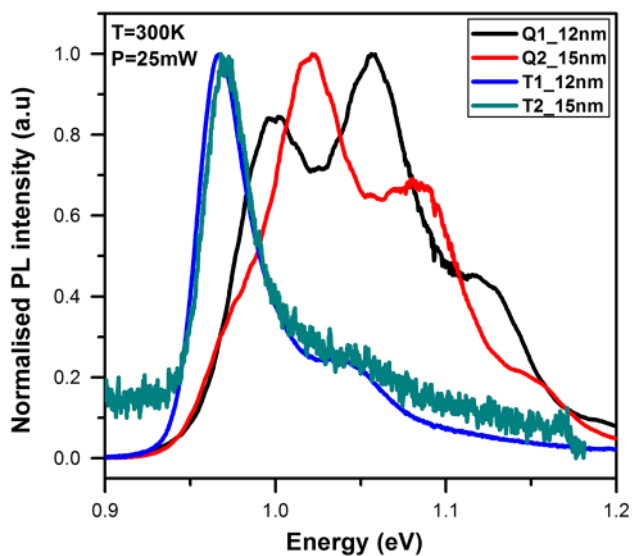


Fig. 4 Normalized room-temperature (300 K) PL spectra at an excitation power of 25 mW as a function of energy